

Form PTO 1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

211897US99

SERIAL NO.

09/911,496

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Robert J. HIGGINS, et al.

FILING DATE

July 25, 2001

GROUP

2814

U.S. PATENT DOCUMENTS

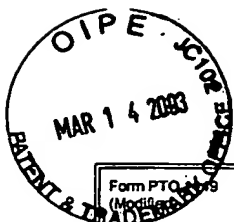
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NR	AA	3,802,967	04/09/74	Ladany et al.			
	AB	4,174,422	11/13/79	Matthews et al.			
	AC	4,404,265	09/13/83	Manasevit			
	AD	4,482,906	11/13/84	Hovel et al.			
	AE	4,523,211	06/11/85	Morimoto et al.			
	AF	4,661,176	04/28/87	Manasevit			
	AG	4,793,872	12/27/88	Meunier et al.			
	AH	4,846,926	07/11/89	Kay et al.			
	AJ	4,855,249	08/08/89	Akasaki et al.			
	AI	4,891,091	01/02/90	Shastri			
	AK	4,912,087	03/27/90	Aslam et al.			
	AL	4,928,154	05/22/90	Umeno et al.			
	AM	4,963,949	10/16/90	Wanlass et al.			
	AN	5,141,894	08/25/92	Bisaro et al.			
	AO	5,159,413	10/27/92	Calviello et al.			
	AP	5,173,474	12/22/92	Connell et al.			
	AQ	5,221,367	06/22/93	Chisholm et al.			
	AR	5,225,031	07/06/93	McKee et al.			
	AS	5,358,925	10/25/94	Neville Connell et al.			
	AT	5,393,352	02/28/95	Summerfelt			
	AU	5,418,216	05/23/95	Fork			
	AV	5,450,812	09/19/95	McKee et al.			
	AW	5,478,653	12/26/95	Guenzer			
	AX	5,482,003	01/09/96	McKee et al.			
	AY	5,514,484	05/07/96	Nashimoto			
	AZ	5,556,463	09/17/96	Guenzer			
	BA	5,588,995	12/31/96	Sheldon			
	BB	5,670,798	09/23/97	Schetzina			
	BC	5,733,641	03/31/98	Fork et al.			
	BD	5,735,949	04/07/98	Manti et al.			
	BE	5,741,724	04/21/98	Ramdani et al.			
	BF	5,810,923	09/22/98	Yano et al.			
	BG	5,830,270	11/03/98	McKee et al.			
	BH	5,912,068	06/15/99	Jia			
	BI	6,020,222	02/01/00	Wollesen			
	BJ	6,045,626	04/04/00	Yano et al.			
	BK	6,064,078	05/16/00	Northrup et al.			
	BL	6,064,092	05/16/00	Park			
	BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
	BN	6,103,008	08/15/00	McKee et al.			
	BO	6,136,666	10/24/00	So			
	BP	6,174,755	01/16/01	Manning			
AB	BQ	6,180,486	01/30/01	Leobandung et al.			

12/13/05

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 211897US99		SERIAL NO. 09/911,496	
LIST OF REFERENCES CITED BY APPLICANT MAR 14 2003				APPLICANT Robert J. HIGGINS, et al.			
				FILING DATE July 25, 2001		GROUP 2814	
U.S. PATENT DOCUMENTS							
INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
123	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanabe			
	CS	5,436,759	07/25/95	Dijali et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwhah, et al.			
	CV	5,640,267	06/17/97	May et al.			
	CW	5,674,366	10/07/97	Hayashi et al.			
	CX	5,729,641	03/17/98	Chandonnet et al.			
	CY	5,790,583	08/04/98	Ho			
	CZ	5,825,799	10/20/98	Ho et al.			
	DA	5,857,049	01/05/99	Beranek et al.			
	DB	5,874,860	02/23/99	Brunel et al.			
	DC	5,926,496	07/20/99	Ho et al.			
	DD	5,937,285	08/10/99	Abrokwhah, et al.			
	DE	5,981,400	11/09/99	Lo			
	DF	5,990,495	11/23/99	Ohba			
	DG	6,002,375	12/14/99	Corman et al.			
	DH	6,008,762	12/28/99	Nghiem			
	DI	6,055,179	04/25/00	Koganel et al.			
	DJ	6,107,653	08/22/00	Fitzgerald			
	DK	6,113,690	09/05/00	Yu et al.			
	DL	6,114,996	09/05/00	Nghiem			
	DM	6,121,642	09/19/00	Newns			
	DN	6,128,178	10/03/00	Newns			
	DO	6,143,072	11/07/00	McKee et al.			
	DP	6,184,144	02/06/01	Lo			
AB	DQ	6,222,654	04/24/01	Frigo			

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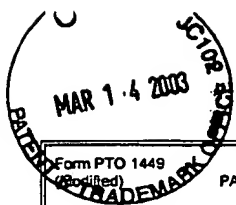
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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Robert J. HIGGINS, et al.			
				FILING DATE July 25, 2001		GROUP 2814	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
RA	EA	4,484,332	11/20/84	Hawrylo			
	EB	4,815,084	03/21/89	Scifres et al.			
	EC	4,876,219	10/24/89	Eshita et al.			
	ED	4,963,508	10/16/90	Umeno et al.			
	EE	5,060,031	10/22/91	Abrokwah, et al.			
	EF	5,063,166	11/05/91	Mooney et al.			
	EG	5,116,461	05/26/92	Lebby et al.			
	EH	5,127,067	06/30/92	Delcoco et al.			
	EI	5,144,409	09/01/92	Ma			
	EJ	5,293,050	03/08/94	Chapple-Sokol et al			
	EK	5,356,831	10/18/94	Calviello et al.			
	EL	5,391,515	02/21/95	Kao et al.			
	EM	5,442,191	08/15/95	Ma			
	EN	5,444,016	08/22/95	Abrokwah, et al.			
	EO	5,480,829	01/02/96	Abrokwah, et al.			
	EP	5,528,414	06/18/96	Oakley			
	EQ	5,614,739	03/25/97	Abrokwah et al.			
	ER	5,729,394	03/17/98	Sevier et al.			
	ES	5,731,220	03/24/98	Tsu et al.			
	ET	5,764,676	06/09/98	Paoli et al.			
	EU	5,777,762	07/07/98	Yamamoto			
	EV	5,778,018	07/07/98	Yoshikawa et al.			
	EW	5,778,116	07/07/98	Tomich			
	EX	5,801,105	09/01/98	Yano et al.			
	EY	5,828,080	10/27/98	Yano et al.			
	EZ	5,858,814	01/12/99	Goossen et al.			
	FA	5,861,966	01/19/99	Ortel			
	FB	5,883,996	03/16/99	Knapp et al.			
	FC	5,995,359	11/30/99	Klee et al.			
	FD	6,058,131	05/02/00	Pan			
	FE	6,137,603	10/24/00	Henmi			
	FF	6,146,906	11/14/00	Inoue et al.			
	FG	6,173,474	01/16/01	Conrad			
	FH	6,180,252	01/30/01	Farrell et al.			
	FI	4,242,595	12/30/0	Lehovec			
	FJ	4,398,342	08/16/83	Pitt et al.			
	FK	4,424,589	01/03/84	Thomas et al.			
	FL	4,876,208	10/24/89	Gustafson et al.			
	FM	4,482,422	11/84	McGinn et al.			
	FN	4,667,088	05/19/87	Kramer			
	FO	4,772,929	09/20/88	Manchester et al.			
	FP	4,841,775	06/27/89	Ikeda et al.			
RA	FQ	4,845,044	07/04/89	Ariyoshi et al.			

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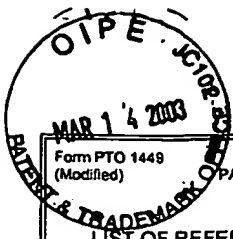
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U.S. PATENT DOCUMENTS

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AB	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pimung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
	HE	5,504,183	04/02/96	Shi			
	HF	5,511,238	04/23/96	Bayraktaroglu			
	HG	5,512,773	04/96	Wolf et al.			
	HH	5,515,047	05/07/96	Yamakido et al.			
HI	5,515,810	05/14/96	Yamashita et al.				
HJ	5,519,235	05/96	Ramesh				
HK	5,549,977	08/96	Jin et al.				
HL	5,551,238	09/03/96	Prueitt				
HM	5,552,547	09/03/96	Shi				
HN	5,589,284	12/31/96	Summerfelt et al.				
HO	5,602,418	02/11/97	Imai et al.				
HP	5,633,724	05/27/97	King et al.				

Richard An

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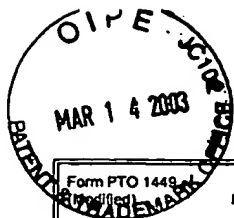
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LIST OF REFERENCES CITED BY APPLICANT

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JLB	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
IU	5,844,260	12/01/98	Ohori				
IV	5,846,846	12/08/98	Suh et al.				
IW	5,863,326	01/26/99	Nause et al.				
IX	5,872,493	02/16/99	Ella				
IY	5,879,956	03/99	Seon et al.				
IZ	5,880,452	03/09/99	Plesko				
JA	5,883,564	03/16/99	Partin				
JB	5,907,792	05/25/99	Droopad et al.				
JC	5,937,274	08/10/99	Kondow et al.				
JD	5,948,161	09/07/99	Kizuki				
JE	5,959,879	09/28/99	Koo				
JF	5,966,323	10/99	Chen et al.				
JG	5,987,011	11/16/99	Toh				
JH	6,022,140	02/08/00	Fraden et al.				
JI	6,022,410	02/08/00	Yu et al.				
JJ	6,023,082	02/08/00	McKee et al.				
JK	6,028,853	02/22/00	Haartsen				
JL	6,049,702	04/11/00	Tham et al.				
JM	6,078,717	06/20/00	Nashimoto et al				
JN	6,088,216	07/00	Laibowitz et al.				
JO	6,090,659	07/00	Laibowitz et al.				
JP	6,107,721	08/22/00	Lakin				
JQ	6,153,010	11/28/00	Kiyoku et al				

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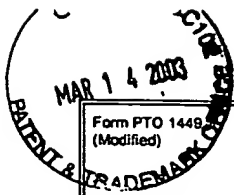


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	KB	6,191,011	02/01	Gilboa et al			
	KC	6,204,737	03/20/01	Ella			
	KD	6,224,669	05/01/01	Yi et al.			
	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	KH	6,313,486	11/01	Kencke et al.			
	KI	6,316,832	11/13/01	Tsuzuki et al.			
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
	KL	4,756,007	07/05/88	Qureshi et al.			
	KM	4,773,063	09/20/88	Hunsperger et al.			
	KN	5,394,489	02/28/95	Koch			
	KO	5,406,202	04/11/95	Mehrgardt et al.			
	KP	5,528,067	06/18/96	Farb et al.			
	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
	KU	6,248,459	06/19/01	Wang et al.			
	KV	6,252,261	06/26/01	Usul et al.			
	KW	6,255,198	07/03/01	Linthicum et al.			
	KX	6,268,269	07/31/01	Lee et al.			
	KY	6,291,319	09/18/01	Yu et al.			
	KZ	6,316,785	11/13/01	Nunoue et al.			
	LA	6,343,171	01/29/02	Yoshimura et al.			
	LB	4,965,649	10/23/90	Zanio et al.			
LC	6,253,649	05/01	Kawahara et al.				
LD	6,211,096	04/01	Aliman et al.				
LE	6,239,449	05/29/01	Fafard et al.				
LF	2001/0013313	08/16/01	Droopad et al.				
LG	6,184,044	02/06/01	Sone et al.				
LH	6,011,646	01/04/00	Mirkarimi et al.				
LI	5,227,196	07/13/93	Itoh				
LJ	6,150,239	11/21/00	Goesele et al.				
LK	5,441,577	08/15/95	Sasaki et al.				
LL	4,459,325	07/10/84	Nozawa et al.				
LM	4,392,297	07/12/83	Little				
LN	4,289,920	09/15/81	Hovel				
LO	5,281,834	01/25/94	Cambou et al.				
LP	4,901,133	02/13/90	Curran et al.				
LQ	5,514,904	05/07/96	Onga et al.				

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12/13/05

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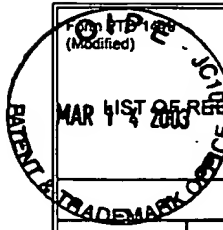
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	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
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	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
	MU	6,372,813	04/16/02	Johnson et al.			
	MV	5,608,046	03/04/97	Cook et al.			
	MW	5,955,591	09/21/99	Imbach et al.			
	MX	6,022,963	02/08/00	McGall et al.			
	MY	6,083,697	07/04/00	Beecher et al.			
	MZ	5,063,081	11/05/91	Cozzette et al.			
	NA	5,479,317	12/26/95	Ramesh			
	NB	5,306,649	04/26/94	Hebert			
	NC	5,962,069	10/05/99	Schindler et al.			
	ND	5,541,422	07/30/96	Wolf et al.			
	NE	5,873,977	02/23/99	Desu et al.			
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	NH	6,235,145	05/22/01	Li et al.			
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	NM	4,439,014	03/27/84	Stacy et al.			
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	NP	6,011,641	01/04/00	Shin et al.			
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		APPLICANT Robert J. HIGGINS, et al.					
		FILING DATE July 25, 2001				GROUP 2814	
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11/2	OA	5,807,440	09/15/98	Kubota et al.	T	T	
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thornton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
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	ON	5,734,672	03/31/98	McMinn et al.			
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	OS	6,134,114	10/17/00	Ungermann et al.			
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	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
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12/13/05

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	QD	6,248,621 B1	06/19/01	Wilk et al.			
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	QF	6,277,436 B1	08/21/01	Stauf et al.			
	QG	6,039,803	03/21/00	Fitzgerald et al.			
	QH	5,619,051	04/08/97	Endo			
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	QK	5,103,494	04/07/92	Mozer			
	QL	4,594,000	06/10/86	Falk et al.			
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	QN	5,244,818	09/14/93	Jokers et al.			
	QO	6,048,751	04/11/00	D'Asaro et al.			
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12/13/05

Form PTO 1449

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ATTY DOCKET NO.

211897US99

SERIAL NO.

09/911,496

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Robert J. HIGGINS, et al.

FILING DATE

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	TO	6,139,483	10/31/00	Seabaugh et al.			
	TP	5,283,462	02/01/94	Stengel			
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12/13/05

Form PTO 1449
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PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

211897US99

SERIAL NO.

09/911,496

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Robert J. HIGGINS, et al.

FILING DATE

July 25, 2001

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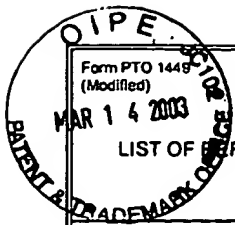
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	UB	5,427,988	06/27/95	Sengupta et al.			
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	UD	5,682,046	10/28/97	Takahashi et al.			
	UE	5,181,085	01/19/93	Moon et al.			
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	UG	6,013,553	01/11/00	Wallace et al.			
	UH	4,872,046	10/03/89	Morkoc et al.			
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AM	UR	6,194,753 B1	02/27/01	Seon et al.			
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Richard AN

12/13/05

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

211897US99

SERIAL NO.

09/911,496

APPLICANT

Robert J. HIGGINS, et al.

FILING DATE

July 25, 2001

GROUP

2814

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Michael A. H.

12/13/05

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

SERIAL NO.

211897US99

09/911,496

APPLICANT

Robert J. HIGGINS, et al.

FILING DATE

July 25, 2001

GROUP

2814

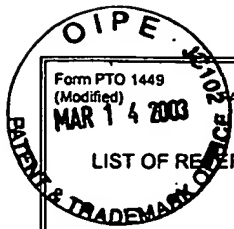
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Richardson

12/13/05



Form PTO 1449

(Modified)

MAR 14 2003

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

211897US99

SERIAL NO.

09/911,496

APPLICANT

Robert J. HIGGINS, et al.

FILING DATE

July 25, 2001

GROUP

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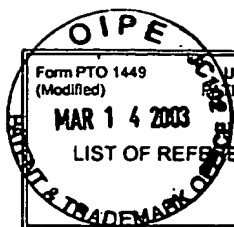
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	CAJ	WO 02/03480	01/10/02	WIPO		
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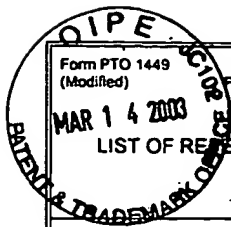
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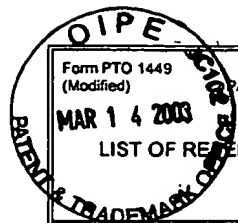
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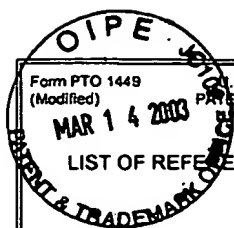
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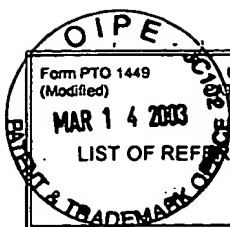
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Robert J. HIGGINS, et al.

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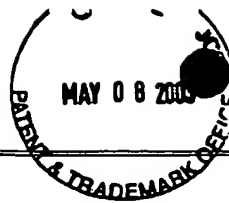
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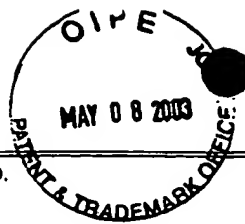
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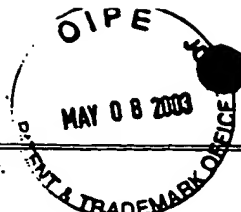
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	UW	6,110,813	08/29/00	Ota et al.			
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	VY	2002/0195610 A1	12/26/02	Klosowiak			
	VZ	5,477,363	12/19/95	Matsuda			
	WA	5,905,571	05/18/99	Butler et al.			
	WB	5,570,226	10/29/96	Ota			
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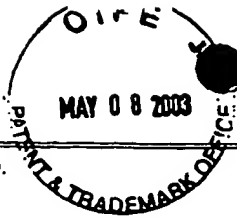
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Robert J. Higgins

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	YK	6,538,359 B1	03/25/03	HIRAKU ET AL			
	YL	6,498,358 B1	12/24/02	LACH ET AL			
	YM	5,387,811	02/07/95	SAIGOH			
	YN	5,523,602	06/04/96	HORIUCHI ET AL			
	YO	5,362,998	11/08/94	IWAMURA ET AL			
	YP	5,168,976	02/23/93	KUME ET AL			

Examiner

Date Considered

12/13/05

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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Robert J. HIGGINS, et al.			
				FILING DATE July 25, 2001		GROUP 2814	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
NB	YQ	6,501,121 B1	12/31/02	YU ET AL			
	YR	5,919,515	07/06/99	YANO ET AL			
	YS	5,238,877	08/24/93	RUSSELL			
	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
	YY	2002/0021855	02/21/02	KIM			
	YZ	6,110,840	08/29/00	YU			
	ZA	5,667,586	09/16/97	EK ET AL			
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
	ZC	5,315,128	05/24/94	HUNT ET AL			
	ZD	5,919,522	07/06/99	BAUM ET AL			
	ZE	4,843,609	06/27/89	OHYA ET AL			
	ZF	4,626,878	12/02/86	KUWANO ET AL			
	ZG	4,525,871	06/25/85	FOYT ET AL			
	ZH	3,818,451	06/18/74	COLEMAN			
	ZI	6,059,895	05/09/00	CHU ET AL			
	ZJ	4,447,116	05/08/84	KING ET AL			
	ZK	6,022,671	02/08/00	BINKLEY ET AL			
	ZL	5,754,714	05/19/98	SUZUKI ET AL			
	ZM	6,524,651 B2	02/25/03	GAN ET AL			
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL			
	ZO	5,642,371	06/24/97	TOHYAMA ET AL			
	ZP	6,445,724 B2	09/03/02	ABELES			
	ZQ	5,753,934	05/19/98	YANO ET AL			
	ZR	6,326,667 B1	12/04/01	SUGIYAMA ET AL			
	ZS	6,051,874	04/18/00	MASUDA			
	NT	5,166,761	11/24/92	OLSON ET AL			
	NB	ZU	5,574,744	11/12/96	GAW ET AL		
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APPLICANT

Robert J. HIGGINS, et al.

FILING DATE

July 25, 2001

GROUP

2814

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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
LAB	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT		
	CCB	2 152 315	07/31/85	GREAT BRITAIN		
	CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT		
	CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)		
	CCE	WO 03/012874	02/13/03	WIPO		
	CCF	1 043 427	10/11/00	EUROPE		
	CCG	1 069 605	01/17/01	EUROPE		
	CCH	WO 02/099885	12/12/02	WIPO		
	CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT		
	CCJ	59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)		
	CCK	03046384	02/27/91	JAPAN (ENGLISH ABSTRACT)		
	CCL	WO 02/11254	02/07/02	WIPO		
	CCM	0 494 514	07/15/92	EUROPE		
	CCN	0 247 722	12/02/87	EUROPE		
	CCO	1 037 272	09/20/00	EUROPE		
	CCP	59-073498	04/25/84	JAPAN (ENGLISH ABSTRACT)		
	CCQ	60-161635	08/23/85	JAPAN W/ENGLISH ABSTRACT		
	CCR	59-044004	03/12/84	JAPAN W/ENGLISH ABSTRACT		
AB	CCS	0 392 714	10/17/90	EUROPE		
	CCT					
	CCU					
	CCV					
	CCW					
	CCX					
	CCY					
	CCZ					
	CDA					
	CDB					
	CDC					
	CDD					
	CDE					
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
LLAA	Peter Weiss; "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3						
LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001						
LLAC	Lori Valigra; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001pp. 1-3						
LLAD	"Holy Grail! Motorola Claims High-Yield GaAs Breakthrough"; Micromagazine.com (no date available); pp. 1-3						
LLAE	Jong-Gul YOON; "Growth of Ferroelectric LiNbO ₃ Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651						
LLAF	V. Bormand et al.; "Deposition of LiTaO ₃ thin films by pyrosol process"; Thin Solid Films 304 (1997); pp.239-244						
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LLAI	Dwight C. Streit et al; "High Reliability GaAs-AlGaAs HBT's by MBE with Be Base Doping and InGaAs Emitter Contacts"; 8179 IEEE Electron Device Letters; 12(1991) September, No. 9, New York, US						
LLAJ	C. Y. Hung et al; "Piezoelectrically induced stress tuning of electro-optic devices"; 320 Applied Physics Letters; 59(1991) 30 December, No. 27, New York, US						
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LLAL	P. Mackowiak et al.; "Some aspects of designing an efficient nitride VCSEL resonator"; J. Phys. D: Appl. Phys. 34(2001); pp. 954-958						
LLAM	M.R. Wilson et al.; GaAs-On-Si: A GaAs IC Manufacturer's Perspective"; GaAs IC Symposium, IEEE, 1988; pp. 243-246						
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LLAP							
LLAQ							
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RLS	ZV	5,122,679	06/16/92	ISHII ET AL			
	ZW	6,232,806	05/15/01	WOESTE ET AL			
	ZX	5,430,397	07/04/95	ITOH ET AL			
	ZY	6,151,240	11/21/00	SUZUKI			
	ZZ	6,528,374	03/04/03	BOJARCZUK, JR ET AL			
	A1	6,589,887	07/08/03	DALTON ET AL			
	A2	5,064,781	11/12/91	CAMBOU ET AL			
	A3	2002/0052061	05/02/02	FITZGERALD			
	A4	5,696,392	12/09/97	CHAR ET AL			
	A5	5,986,301	11/16/99	FUKUSHIMA ET AL			
RLS	A6	6,329,277	12/11/01	LIU ET AL			
	A7						
	A8						
	A9						
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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
RLS	CCS	WO 99/67882	12/29/99	WIPO			
	CCT	WO 95/02904	01/26/95	WIPO			
	CCU	WO 02/009150	01/31/02	WIPO			
	CCV	0 766 292	04/02/97	EUROPE			
	CCW	198 29 609	01/05/00	GERMANY			
	CCX	1 069 605	01/17/01	EUROPE			
	CCY	0 828 287	03/11/98	EUROPE			
RLS	CCZ	1 176 230	01/30/02	EUROPE			
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RLS	LLAP	YI W. et al; "Mechanism of cleaning Si (100) surface using Sr and SrO for the growth of crystalline SrTiO/sub 2/films" Journal of Vacuum Science & Technology, Vol. 20, No. 4, July 2002 (2002-07) pp. 1402-1405					
RLS	LLAQ	XIAMING HU et al; "Sr/Si template formation for the epitaxial growth of SrTiO/sub 3/on silicon" Materials Research Society Proceedings, Vol. 716, 2002, pp. 261-266					
	LLAR						
	LLAS						<input type="checkbox"/> Additional References sheet(s) attached
Examiner <i>[Signature]</i>					Date Considered 12/13/05		
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